

2MBI600VE-120-50

IGBT Modules

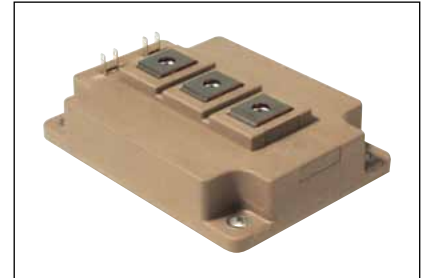
IGBT MODULE (V series) 1200V / 600A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units
Collector-Emitter voltage	V _{CEs}		1200	V
Gate-Emitter voltage	V _{GES}		±20	V
Inverter Collector current	I _c	Continuous	T _c =100°C	600
			T _c =25°C	700
	I _c pulse	1ms	1200	
	-I _c		600	
	-I _c pulse	1ms	1200	
Collector power dissipation	P _c	1 device	4800	W
Junction temperature	T _j		175	°C
Operating junction temperature (under switching conditions)	T _{jop}		150	
Case temperature	T _c		125	
Storage temperature	T _{stg}		-40 ~ +125	
Isolation voltage	V _{iso}	AC : 1min.	2500	VAC
Screw torque	Mounting (*2)		6.0	N m
	Terminals (*3)		5.0	

Note *1: All terminals should be connected together during the test.

Note *2: Recommendable Value : 3.0-6.0 Nm (M5 or M6)

Note *3: Recommendable Value : 2.5-5.0 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CEs}	V _{GE} = 0V, V _{CE} = 1200V	-	-	2.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	800	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 600mA	6.0	6.5	7.0	V	
Inverter Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 600A	T _j =25°C	-	2.05	2.55	V
			T _j =125°C	-	2.40	-	
	T _j =150°C		-	2.45	-		
	V _{CE(sat)} (chip)		T _j =25°C	-	1.75	2.15	
	T _j =125°C		-	2.05	-		
T _j =150°C	-	2.10	-				
Internal gate resistance	R _{g(int)}	-	-	1.3	-	Ω	
Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	48.5	-	nF	
Inverter Turn-on time	ton	V _{CC} = 600V L _s = 30nH	-	0.60	-	μsec	
	tr	I _c = 600A	-	0.20	-		
tr (i)	V _{GE} = ±15V	-	0.05	-			
Turn-off time	toff	R _G = 0.62Ω	-	0.80	-	μsec	
	tf	T _j = 150°C	-	0.08	-		
Inverter Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 600A	T _j =25°C	-	1.85	2.45	V
			T _j =125°C	-	2.00	-	
	T _j =150°C		-	1.95	-		
	V _F (chip)		T _j =25°C	-	1.70	2.15	
	T _j =125°C		-	1.85	-		
T _j =150°C	-	1.80	-				
Reverse recovery time	t _{rr}	I _F = 600A	-	0.15	-	μsec	

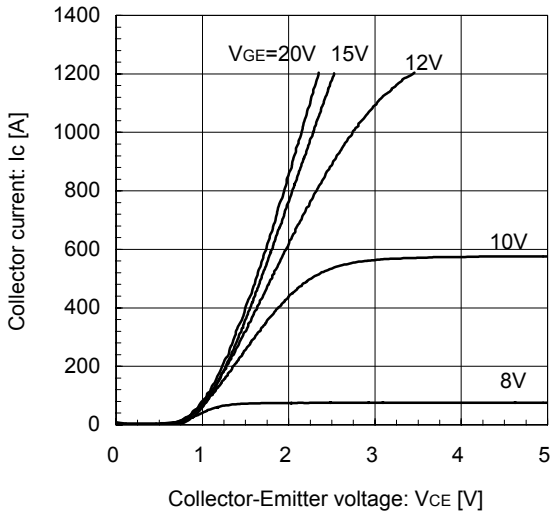
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	IGBT	-	-	0.031	°C/W
		FWD	-	-	0.054	
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.0125	-	

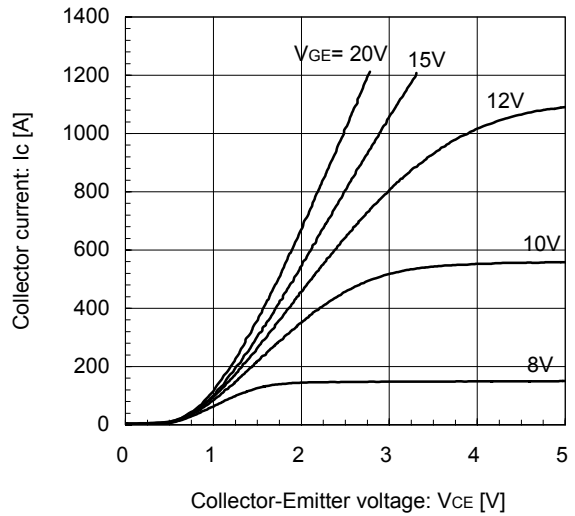
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

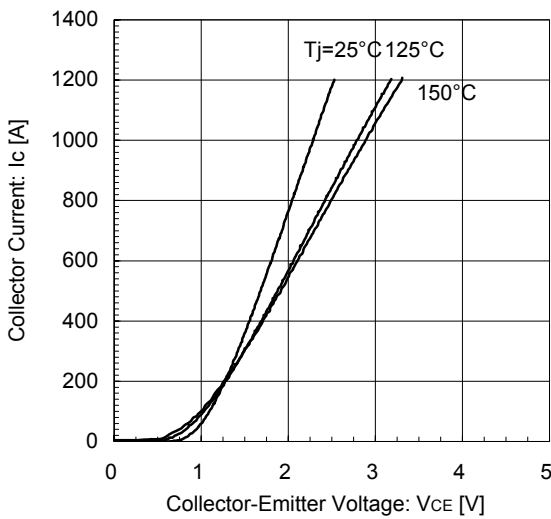
Collector current vs. Collector-Emittor voltage (typ.)
T_j = 25°C / chip



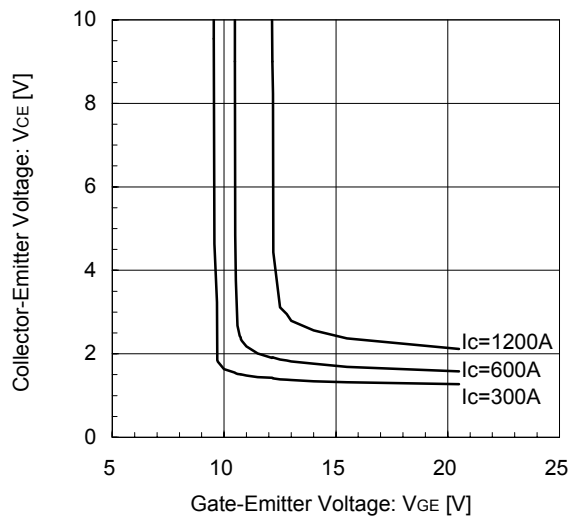
Collector current vs. Collector-Emittor voltage (typ.)
T_j = 150°C / chip



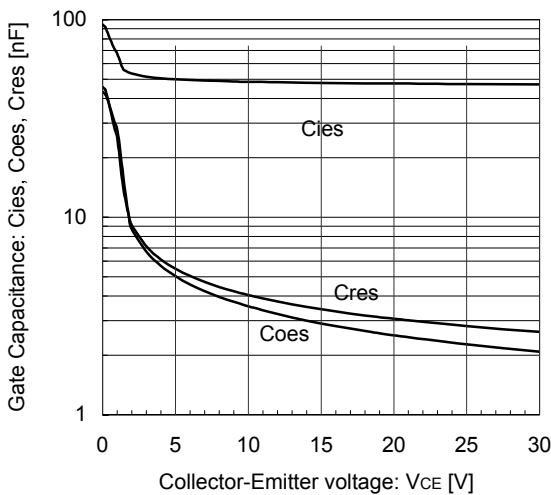
Collector current vs. Collector-Emittor voltage (typ.)
V_{GE} = 15V / chip



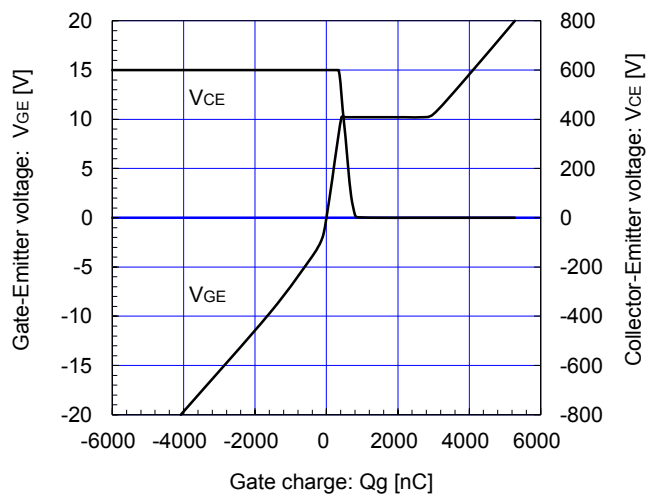
Collector-Emittor voltage vs. Gate-Emittor voltage
T_j = 25°C / chip



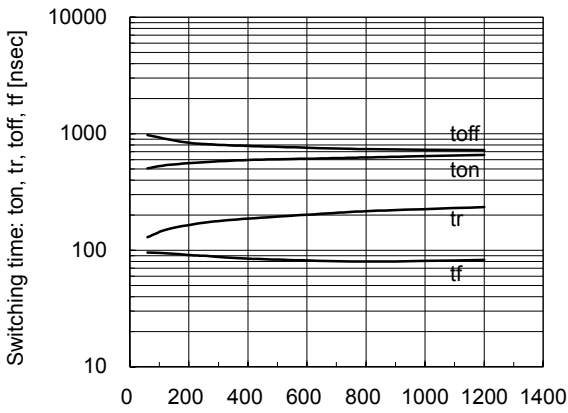
Gate Capacitance vs. Collector-Emittor Voltage
V_{GE} = 0V, f = 1MHz, T_j = 25°C



Dynamic Gate Charge (typ.)
V_{CC} = 600V, I_c = 600A, T_j = 25°C

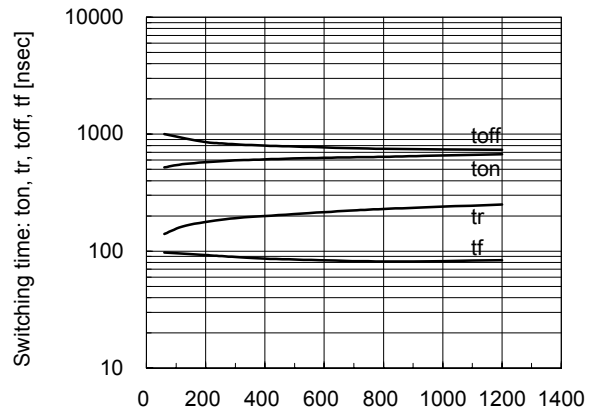


Switching time vs. Collector current (typ.)
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=0.62\Omega, T_j=125^\circ C$



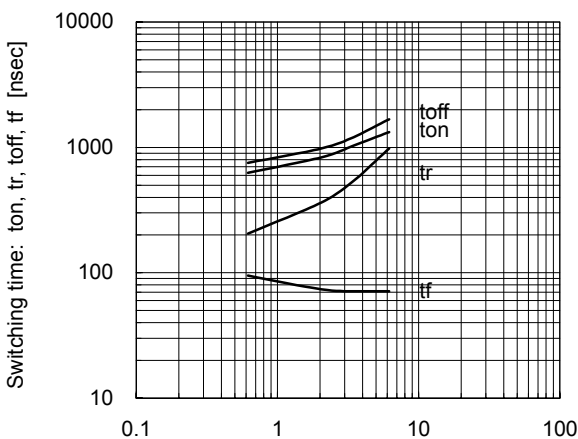
Collector current: I_c [A]

Switching time vs. Collector current (typ.)
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=0.62\Omega, T_j=150^\circ C$



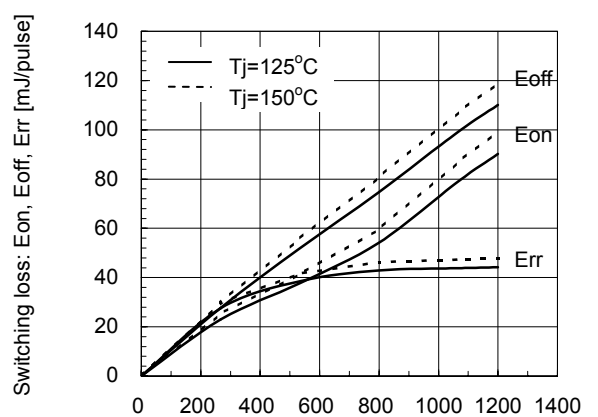
Collector current: I_c [A]

Switching time vs. Gate resistance (typ.)
 $V_{CC}=600V, I_c=600A, V_{GE}=\pm 15V, T_j=125^\circ C$



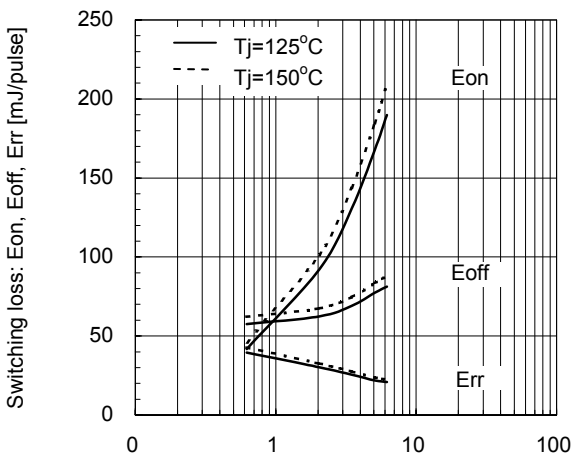
Gate resistance: R_G [Ω]

Switching loss vs. Collector current (typ.)
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=0.62\Omega, T_j=125^\circ C, 150^\circ C$



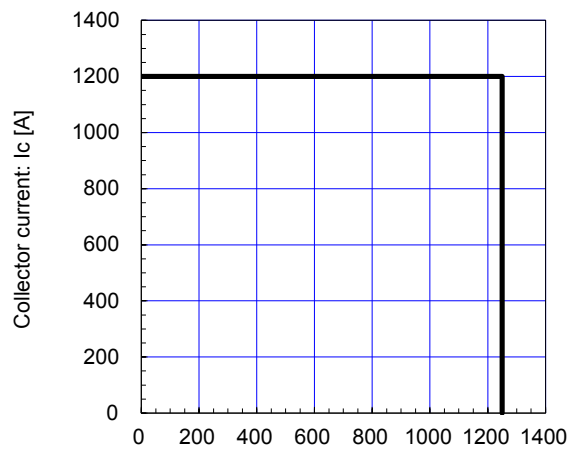
Collector current: I_c [A]

Switching loss vs. Gate resistance (typ.)
 $V_{CC}=600V, I_c=600A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



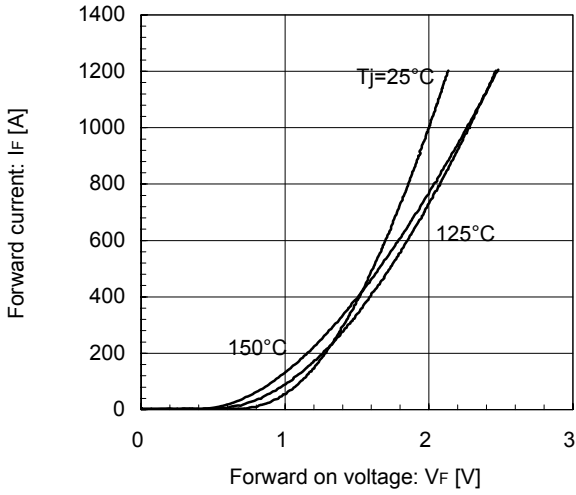
Gate resistance: R_G [Ω]

Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=15V, R_G=0.62\Omega, T_j=150^\circ C$

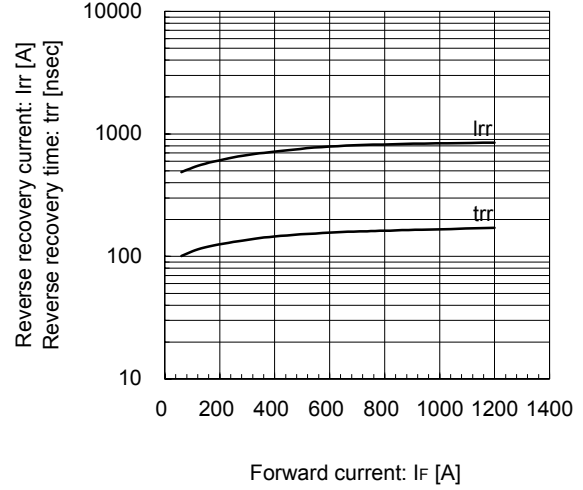


Collector-Emitter voltage: V_{CE} [V]
 (Main terminals)

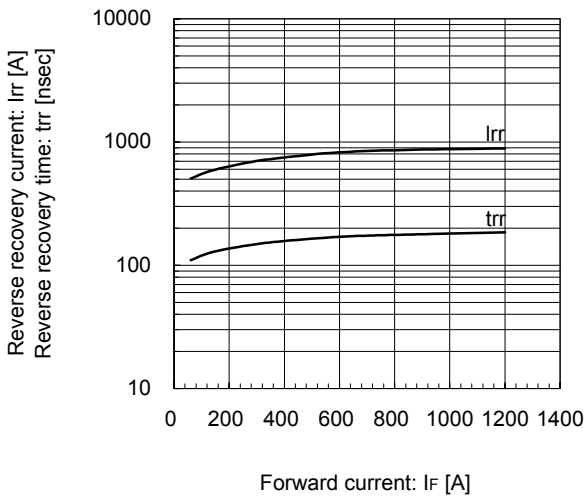
Forward Current vs. Forward Voltage (typ.)
chip



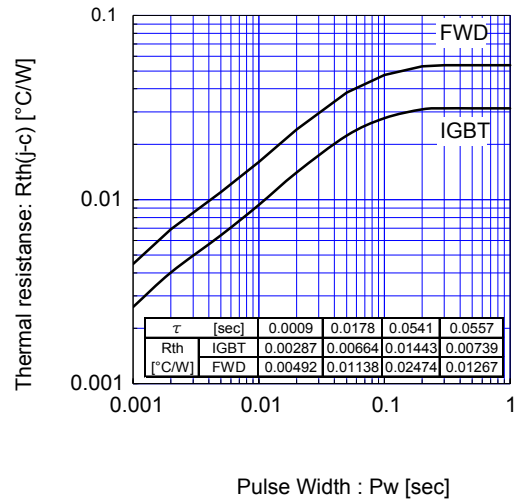
Reverse Recovery Characteristics (typ.)
Vcc=600V, VGE=±15V, RG=0.62Ω, Tj=125°C



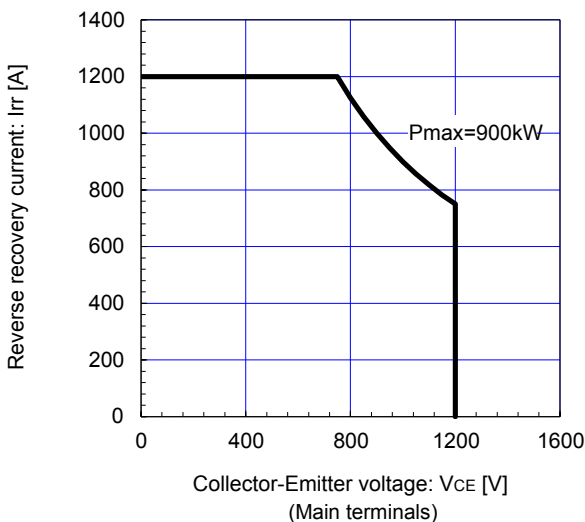
Reverse Recovery Characteristics (typ.)
Vcc=600V, VGE=±15V, RG=0.62Ω, Tj=150°C



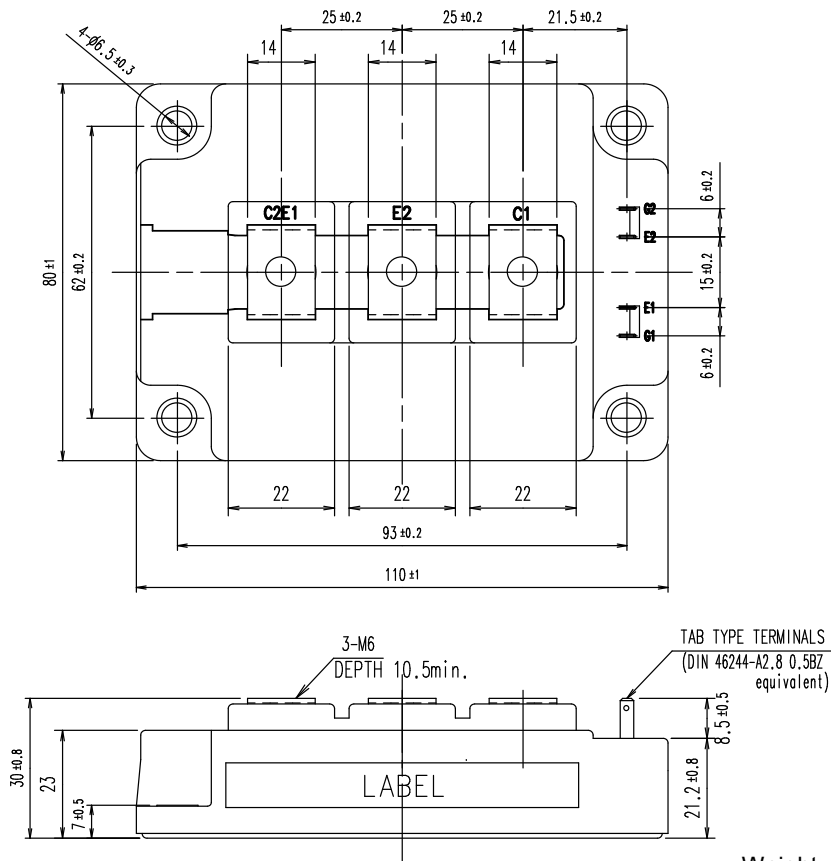
Transient Thermal Resistance (max.)



FWD safe operating area (max.)
Tj=150°C

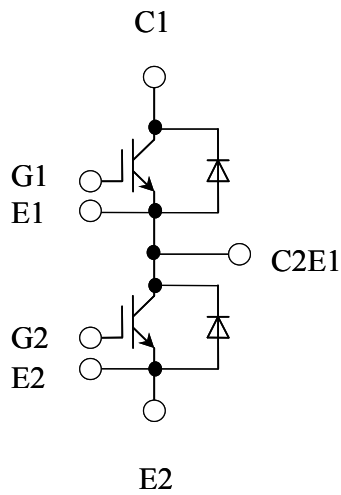


■ Outline Drawings (Unit: mm)



Weight: 470g (typ.)

■ Equivalent Circuit



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